

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

#### **Listing of Claims:**

Claims 1-2 (canceled).

Claim 3 (previously presented): A sputtering target for forming a seed layer of a semiconductor device, comprising: a copper alloy sputtering target containing 0.2 to 5 wt% of Al and having a sputtering face, said target having a structure that does not substantially contain any precipitates and a resistivity of  $2.2 \mu \Omega \text{ cm}$  or more, said target having a ratio  $I(111)/I(200)$  of an X-ray diffraction peak intensity  $I(111)$  of a (111) face and an X-ray diffraction peak intensity  $I(200)$  of a (200) face of 2.2 or more in said sputtering face, and variation in  $I(111)/I(200)$  in said sputtering face is respectively within  $\pm 30\%$ .

Claim 4 (original): A copper alloy sputtering target according to claim 3, wherein said target contains 0.5 to 1 wt% of Al.

Claims 5-6 (canceled).

Claim 7 (previously presented): A sputtering target for forming a seed layer of a semiconductor device, comprising: a copper alloy sputtering target containing a total of 0.2 to 5 wt% of an alloying component of Al and having a sputtering face, said target having a structure that does not substantially contain any precipitates and a resistivity of greater than a resistivity of

a copper alloy having the same composition in a thermal equilibrium state, wherein a ratio  $I(111)/I(200)$  of an X-ray diffraction peak intensity  $I(111)$  of a (111) face and an X-ray diffraction peak intensity  $I(200)$  of a (200) face is 2.2 or more in said sputtering face, and variation in  $I(111)/I(200)$  in said sputtering face is respectively within  $\pm 30\%$ .

Claim 8 (previously presented): A copper alloy sputtering target according to claim 7, wherein said target contains a total of 0.5 to 1 wt% of Al.

Claims 9-15 (canceled).

Claim 16 (previously presented): A copper alloy sputtering target according to claim 7, wherein an increase in resistivity due to said alloying component in said target is 1.2 times or more than that of said copper alloy in said thermal equilibrium state.

Claim 17 (previously presented): A copper alloy sputtering target according to claim 7, wherein said target has a crystal grain size of  $50\mu\text{m}$  or less, and variation in average grain size by location is within  $\pm 20\%$ .

Claim 18 (previously presented): A copper alloy sputtering target according to claim 7, wherein variation in said alloying component of said target is within 0.2%.

Claim 19 (previously presented): A copper alloy sputtering target according to claim 7, wherein each of Na and K contained within said target is 0.1 ppm or less; each of Fe, Ni, Cr and

Ca contained within said target is 1 ppm or less; each of U and Th contained within said target is 1 ppb or less, oxygen contained in said target is 5 ppm or less, hydrogen contained in said target is 2 ppm or less; and unavoidable impurities excluding alloying elements are 10 ppm or less.

Claims 20-22 (canceled).

Claim 23 (previously presented): A copper alloy sputtering target according to claim 3, wherein each of Na and K contained within said target is 0.5 ppm or less; each of Fe, Ni, Cr and Ca contained within said target is 2 ppm or less; each of U and Th contained within said target is 1 ppb or less, oxygen contained in said target is 5 ppm or less, hydrogen contained in said target is 2 ppm or less; and unavoidable impurities excluding alloying elements are 50 ppm or less.

Claim 24 (previously presented): A copper alloy sputtering target according to claim 3, wherein said target has a crystal grain size of  $50\mu\text{m}$  or less, and variation in average grain size by location is within  $\pm 20\%$ .

Claims 25-26 (canceled).

Claim 27 (previously presented): A copper alloy sputtering target according to claim 3, prepared by a process comprising the steps of:

obtaining a high purity copper alloy ingot by vacuum melting;

performing at least one of hot forging and hot rolling to said high purity copper alloy ingot;

thereafter, cold rolling said high purity copper alloy; and  
thereafter sandwiching said high purity copper alloy with copper plates  
underwater and performing forced cooling thereto.

Claim 28 (new): A copper alloy sputtering target for forming a seed layer of a semiconductor device, comprising:

a sputtering target body consisting of copper and 0.2 to 5 wt% of Al, said body  
containing no precipitates and having a sputtering face and a resistivity of  
 $2.2 \mu \Omega \text{ cm}$  or more;

said target having a ratio  $I(111)/I(200)$  of an X-ray diffraction peak intensity  
 $I(111)$  of a (111) face and an X-ray diffraction peak intensity  $I(200)$  of a  
(200) face of 2.2 or more in said sputtering face, and a variation in  
 $I(111)/I(200)$  in said sputtering face of respectively within  $\pm 30\%$ .